Abstract Submitted
for the MAR09 Meeting of
The American Physical Society

Doping effect of electrode on Graphene[1] KEYU PI, KATHY MCCREARY, WEI HAN , YAN LI, WENZHONG BAO, CHUN NING LAU, ROLAND KAWAKAMI, University of California, Riverside, ROLAND, KAWAKAMI TEAM, CHUN-NING, LAU COLLABORATION — Graphene as a carrier tunable transport media has drawn a lot of interest since its discovery. It has recently been reported that invasive electrode contacts cause electron-hole asymmetry [1] which will affect the transport properties. To study this effect, we developed an in-situ measurement system that combines Molecular Beam Epitaxy (MBE) with transport measurement. Fine control of the material deposition rate allows us to study the doping effect on graphene at the early stages of electrode formation. [1] B. Huard et al., PRB. **78**. 121402(R), 2008

[1]We acknowledge the support of ONR,NSF and CNID.

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Date submitted: 31 Dec 2008 Electronic form version 1.4